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ON Semiconductor®

# FQP2P40

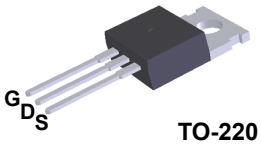
## P-Channel QFET® MOSFET
**-400 V, -2.0 A, 6.5 Ω**

### Description

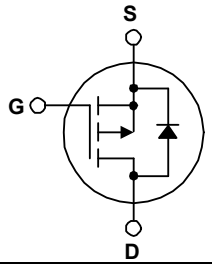
These P-Channel enhancement mode power field effect transistors are produced using ON Semiconductor's proprietary, planar stripe, DMOS technology.
This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for electronic lamp ballast based on complimentary half bridge.

### Features

- -2.0 A, -400 V, $R_{DS(on)}$ = 6.5 Ω (Max.) @ $V_{GS}$ = -10 V
- Low Gate Charge (Typ. 10 nC)
- Low Crss (Typ. 6.5 pF)
- Fast Switching
- 100% Avalanche Tested
- Improved dv/dt Capability




TO-220




### Absolute Maximum Ratings

$T_C$ = 25°C unless otherwise noted.

| Symbol | Parameter | | FQP2P40-F080 | Unit |
|---|---|---|---|---|
| $V_{DSS}$ | Drain-Source Voltage | | -400 | V |
| $I_D$ | Drain Current - Continuous ($T_C$ = 25°C) | | -2.0 | A |
| | - Continuous ($T_C$ = 100°C) | | -1.27 | A |
| $I_{DM}$ | Drain Current - Pulsed | (Note 1) | -8.0 | A |
| $V_{GSS}$ | Gate-Source Voltage | | ± 30 | V |
| $E_{AS}$ | Single Pulsed Avalanche Energy | (Note 2) | 120 | mJ |
| $I_{AR}$ | Avalanche Current | (Note 1) | -2.0 | A |
| $E_{AR}$ | Repetitive Avalanche Energy | (Note 1) | 6.3 | mJ |
| dv/dt | Peak Diode Recovery dv/dt | (Note 3) | -4.5 | V/ns |
| $P_D$ | Power Dissipation ($T_C$ = 25°C) | | 63 | W |
| | - Derate Above 25°C | | 0.51 | W/°C |
| $T_J$, $T_{STG}$ | Operating and Storage Temperature Range | | -55 to +150 | °C |
| $T_L$ | Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds | | 300 | °C |

### Thermal Characteristics

| Symbol | Parameter | FQP2P40-F080 | Unit |
|---|---|---|---|
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case, Max. | 1.98 | °C/W |
| $R_{\theta CS}$ | Thermal Resistance, Case-to-Sink, Typ. | 0.5 | °C/W |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient, Max. | 62.5 | °C/W |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Publication Order Number:
FQP2P40/D

## Package Marking and Ordering Information

| Part Number | Top Mark | Package | Packing Method | Reel Size | Tape Width | Quantity |
|---|---|---|---|---|---|---|
| FQP2P40-F080 | FQP2P40 | TO-220 | Tube | N/A | N/A | 50 units |

## Elerical Characteristics

$T_C$ = 25°C unless otherwise noted.

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|---|---|---|---|---|---|---|
| **Off Characteristics** | | | | | | |
| $BV_{DSS}$ | Drain-Source Breakdown Voltage | $V_{GS}$ = 0 V, $I_D$ = -250 μA | -400 | -- | -- | V |
| $\Delta BV_{DSS}$ / $\Delta T_J$ | Breakdown Voltage Temperature Coefficient | $I_D$ = -250 μA, Referenced to 25°C | -- | - | -- | V/°C |
| $I_{DSS}$ | Zero Gate Voltage Drain Current | $V_{DS}$ = -400 V, $V_{GS}$ = 0 V | -- | -- | -1 | μA |
| | | $V_{DS}$ = -320 V, $T_C$ = 125°C | -- | -- | -10 | μA |
| $I_{GSSF}$ | Gate-Body Leakage Current, Forward | $V_{GS}$ = -30 V, $V_{DS}$ = 0 V | -- | -- | -100 | nA |
| $I_{GSSR}$ | Gate-Body Leakage Current, Reverse | $V_{GS}$ = 30 V, $V_{DS}$ = 0 V | -- | -- | 100 | nA |
| **On Characteristics** | | | | | | |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS}$ = $V_{GS}$, $I_D$ = -250 μA | -3.0 | -- | -5.0 | V |
| $R_{DS(on)}$ | Static Drain-Source On-Resistance | $V_{GS}$ = -10 V, $I_D$ = -1.0 A | -- | 5.0 | 6.5 | Ω |
| $g_{FS}$ | Forward Transconductance | $V_{DS}$ = -50 V, $I_D$ = -1.0 A | -- | 1.42 | -- | S |
| **Dynamic Characteristics** | | | | | | |
| $C_{iss}$ | Input Capacitance | $V_{DS}$ = -25 V, $V_{GS}$ = 0 V, f = 1.0 MHz | -- | 270 | 350 | pF |
| $C_{oss}$ | Output Capacitance | | -- | 45 | 60 | pF |
| $C_{rss}$ | Reverse Transfer Capacitance | | -- | 6.5 | 8.5 | pF |
| **Switching Characteristics** | | | | | | |
| $t_{d(on)}$ | Turn-On Delay Time | $V_{DD}$ = -200 V, $I_D$ = -2.0 A, $V_{GS}$ = -10 V, $R_G$ = 25 Ω (Note 4) | -- | 9 | 30 | ns |
| $t_r$ | Turn-On Rise Time | | -- | 33 | 75 | ns |
| $t_{d(off)}$ | Turn-Off Delay Time | | -- | 22 | 55 | ns |
| $t_f$ | Turn-Off Fall Time | | -- | 25 | 60 | ns |
| $Q_g$ | Total Gate Charge | $V_{DS}$ = -320 V, $I_D$ = -2.0 A, $V_{GS}$ = -10 V (Note 4) | -- | 10 | 13 | nC |
| $Q_{gs}$ | Gate-Source Charge | | -- | 2.1 | -- | nC |
| $Q_{gd}$ | Gate-Drain Charge | | -- | 5.5 | -- | nC |
| **Drain-Source Diode Characteristics and Maximum Ratings** | | | | | | |
| $I_S$ | Maximum Continuous Drain-Source Diode Forward Current | | -- | -- | -2.0 | A |
| $I_{SM}$ | Maximum Pulsed Drain-Source Diode Forward Current | | -- | -- | -8.0 | A |
| $V_{SD}$ | Drain-Source Diode Forward Voltage | $V_{GS}$ = 0 V, $I_S$ = -2.0 A | -- | -- | -5.0 | V |
| $t_{rr}$ | Reverse Recovery Time | $V_{GS}$ = 0 V, $I_S$ = -2.0 A, $dI_F$ / dt = 100 A/μs | -- | 250 | -- | ns |
| $Q_{rr}$ | Reverse Recovery Charge | | -- | 0.85 | -- | μC |

**Notes:**

1. Repetitive rating : pulse-width limited by maximum junction temperature.
2. L = 52.5 mH, $I_{AS}$ = -2.0 A, $V_{DD}$ = -50 V, $R_G$ = 25 Ω, Starting $T_J$ = 25°C.
3. $I_{SD} \leq$ -2.0 A, di/dt ≤ 200 A/μs, $V_{DD} \leq BV_{DSS,}$ Starting $T_J$ = 25°C.
4. Essentially independent of operating temperature.

## Typical Performance Characteristics

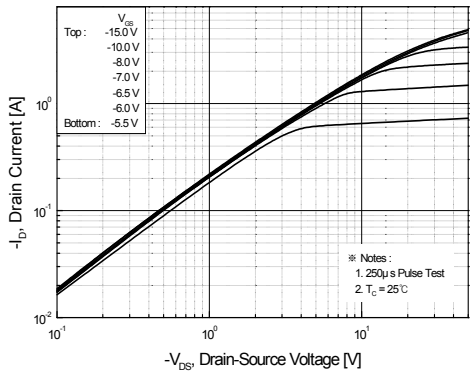


**Figure 1. On-Region Characteristics**

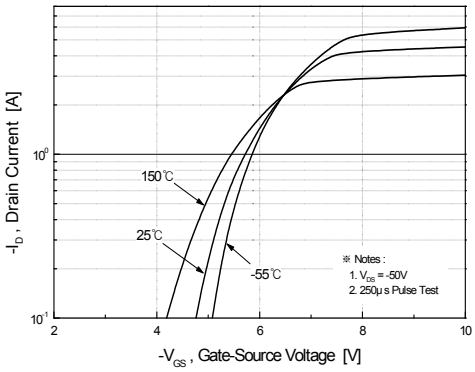


**Figure 2. Transfer Characteristics**

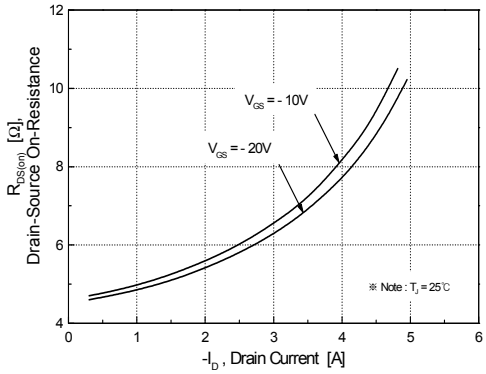


**Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage**

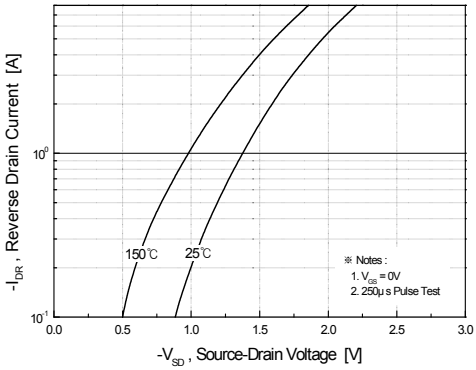


**Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature**

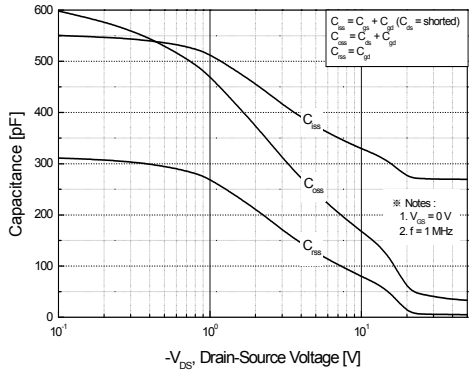


**Figure 5. Capacitance Characteristics**

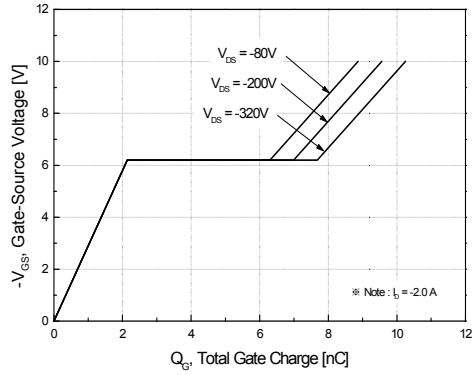


**Figure 6. Gate Charge Characteristics**

## Typical Performance Characteristics (Continued)

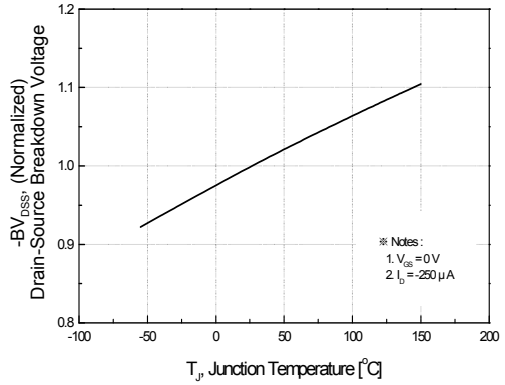


**Figure 7. Breakdown Voltage Variation vs. Temperature**

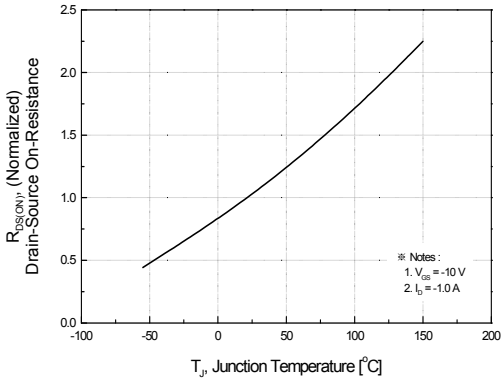


**Figure 8. On-Resistance Variation vs. Temperature**

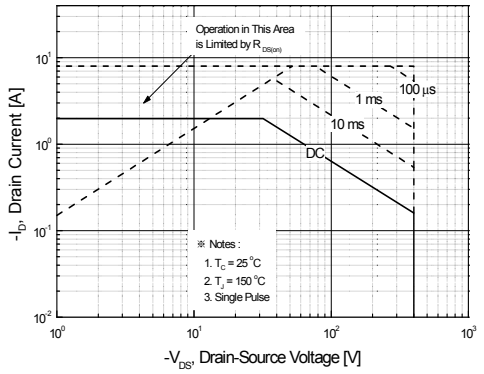


**Figure 9. Maximum Safe Operating Area**

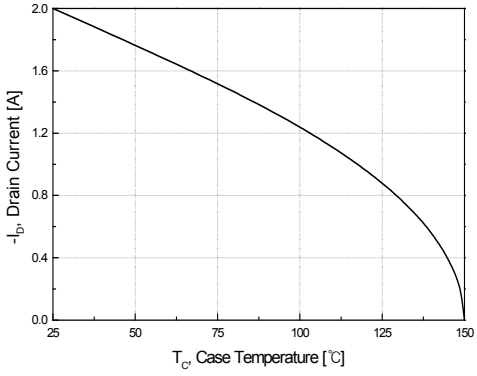


**Figure 10. Maximum Drain Current vs. Case Temperature**

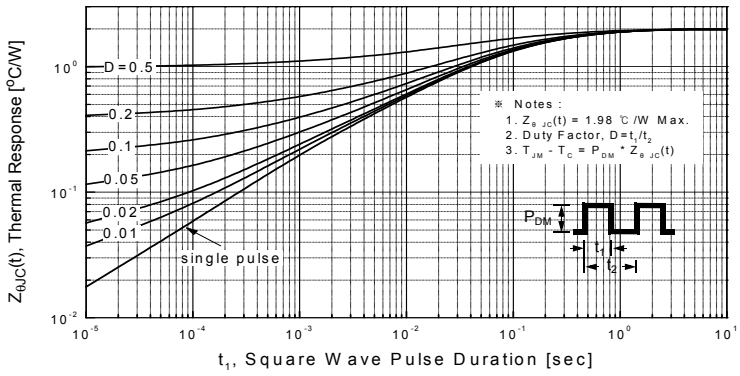


**Figure 11. Transient Thermal Response Curve**

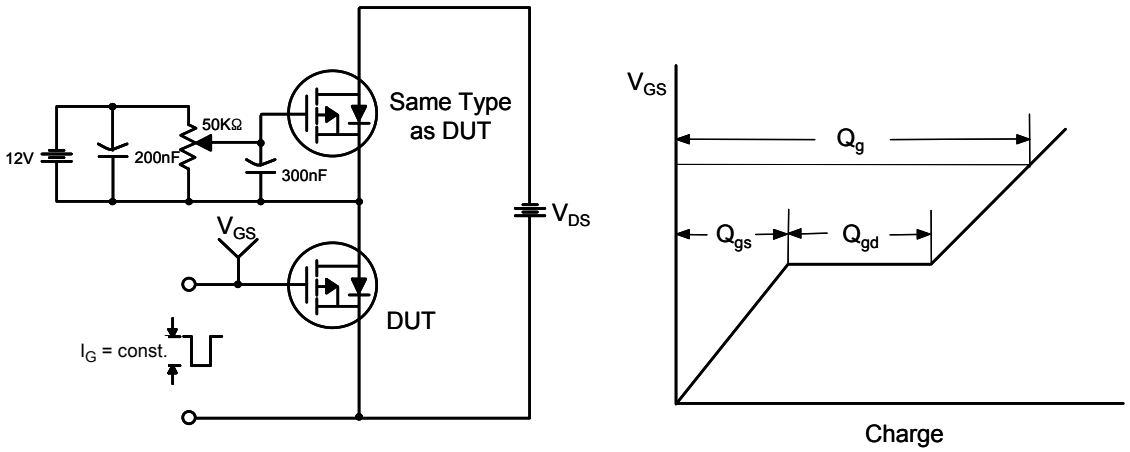


**Figure 12. Gate Charge Test Circuit & Waveform**

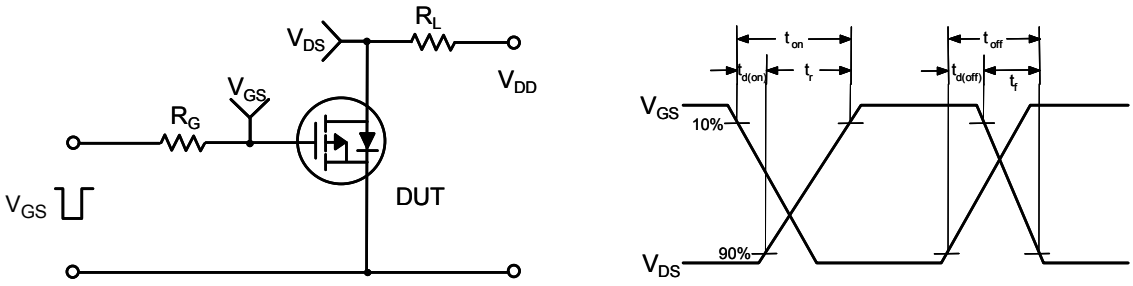


**Figure 13. Resistive Switching Test Circuit & Waveforms**

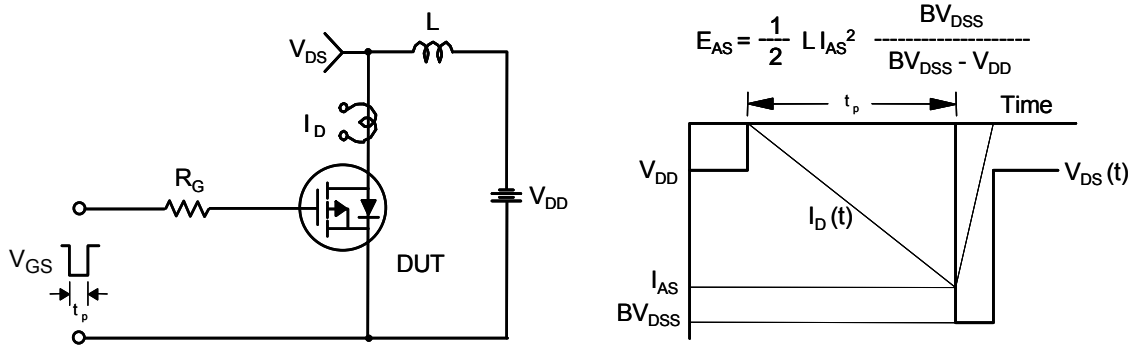


**Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms**

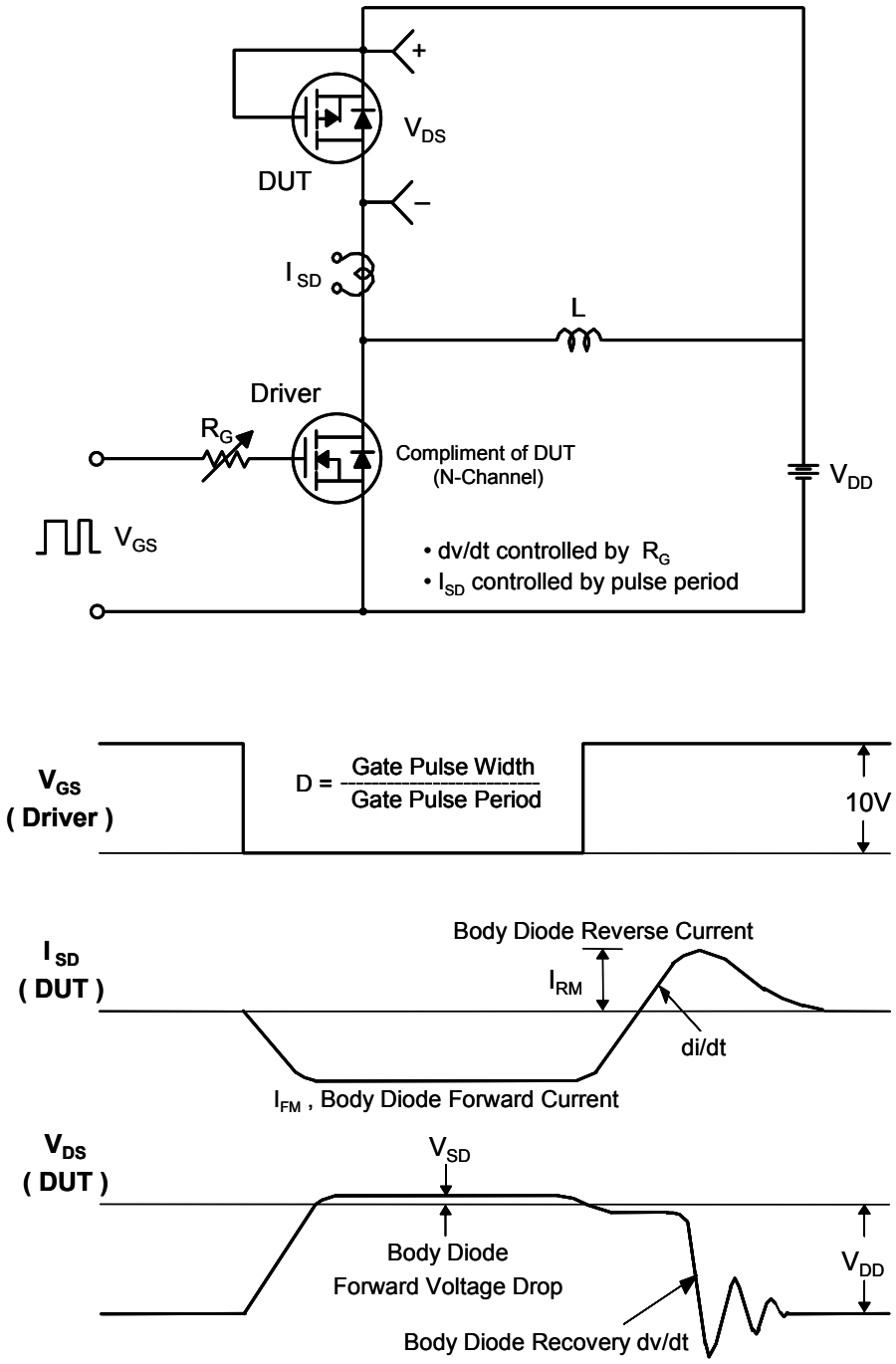


**Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms**

## Mechanical Dimensions

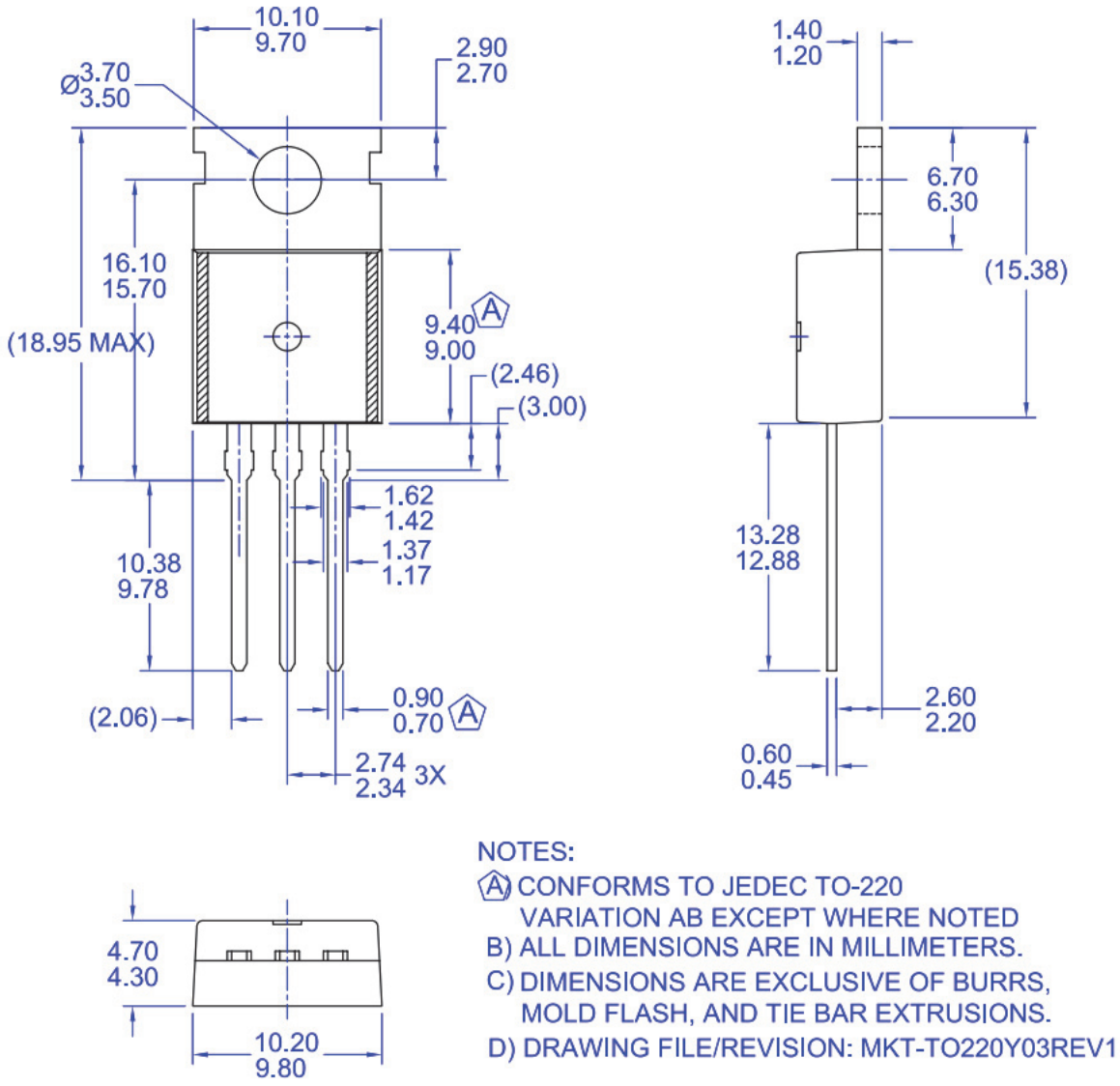


**Figure 16. TO220, Molded, 3-Lead, Jedec Variation AB**

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